**Product data sheet** 

## 1. General description

PNP low  $V_{CEsat}$  transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS304NX

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (hFE) at high I<sub>C</sub>
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Qualified according to AEC-Q101 and recommended for use in automotive applications

# 3. Applications

- · High-voltage DC-to-DC conversion
- High-voltage MOSFET gate driving
- · High-voltage motor control
- · High-voltage power switches (e.g. motors, fans)
- Automotive applications

### 4. Quick reference data

#### Table 1. Quick reference data

| Symbol             | Parameter                               | Conditions  | Min | Тур | Max  | Unit |
|--------------------|---|---|-----|-----|------|------|
| V <sub>CEO</sub>   | collector-emitter voltage               | open base   | -   | -   | -60  | V    |
| I <sub>C</sub>     | collector current                       |   | -   | -   | -4.2 | Α    |
| I <sub>CM</sub>    | peak collector current                  | single pulse; t <sub>p</sub> ≤ 1 ms   | -   | -   | -8.4 | Α    |
| R <sub>CEsat</sub> | collector-emitter saturation resistance | $I_C$ = -4 A; $I_B$ = -200 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C | -   | 48  | 69   | mΩ   |



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# 5. Pinning information

#### **Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline | Graphic symbol                        |
|-----|--------|-------------|--------------------|---------------------------------------|
| 1   | Е      | emitter     |                    | С                                     |
| 2   | С      | collector   |                    | , , , , , , , , , , , , , , , , , , , |
| 3   | В      | base        | 3 2 1              | B—[                                   |
|     |        |             | SOT89              | sym132                                |

# 6. Ordering information

#### **Table 3. Ordering information**

| Type number | Package | ckage  |         |  |  |  |
|-------------|---------|--|---------|--|--|--|
|             | Name    | Description  | Version |  |  |  |
| PBSS304PX-Q |         | plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body | SOT89   |  |  |  |

# 7. Marking

#### Table 4. Marking codes

| Type number | Marking code[1] |
|-------------|-----------------|
| PBSS304PX-Q | %5L             |

[1] % = placeholder for manufacturing site code

# 8. Limiting values

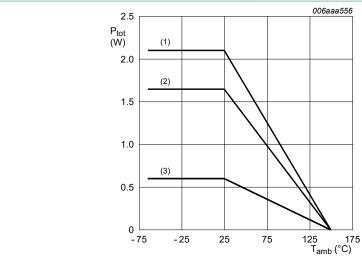
### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                 | Conditions                          |     | Min | Max  | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|------|------|
| V <sub>CBO</sub> | collector-base voltage    | open emitter                        |     | -   | -60  | V    |
| V <sub>CEO</sub> | collector-emitter voltage | open base                           |     | -   | -60  | V    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector                      |     | -   | -5   | V    |
| I <sub>C</sub>   | collector current         |                                     |     | -   | -4.2 | Α    |
| I <sub>CM</sub>  | peak collector current    | single pulse; t <sub>p</sub> ≤ 1 ms |     | -   | -8.4 | Α    |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 0.6  | W    |
|                  |                           |                                     | [2] | -   | 1.65 | W    |
|                  |                           |                                     | [3] | -   | 2.1  | W    |
| Tj               | junction temperature      |                                     |     | -   | 150  | °C   |
| T <sub>amb</sub> | ambient temperature       |                                     |     | -65 | 150  | °C   |
| T <sub>stg</sub> | storage temperature       |                                     |     | -65 | 150  | °C   |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

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- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

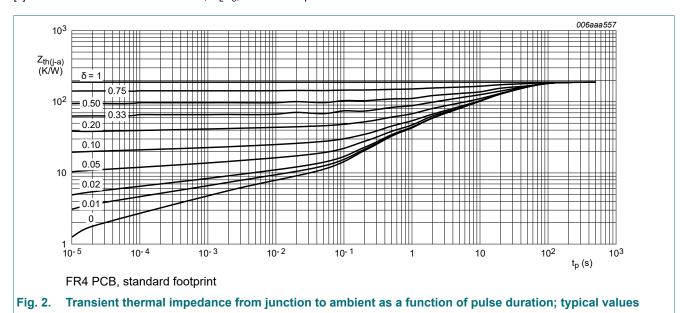
Fig. 1. Power derating curves

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol                | Parameter  | Conditions              |     | Min | Тур | Max | Unit |
|-----------------------|--|-------------------------|-----|-----|-----|-----|------|
| 11(J-a)               | thermal resistance from                          | in free air [1] [2] [3] | [1] | -   | -   | 208 | K/W  |
|                       | junction to ambient                              |                         | [2] | -   | -   | 76  | K/W  |
|                       |  |                         | [3] | -   | -   | 60  | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point |                         |     | -   | -   | 20  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



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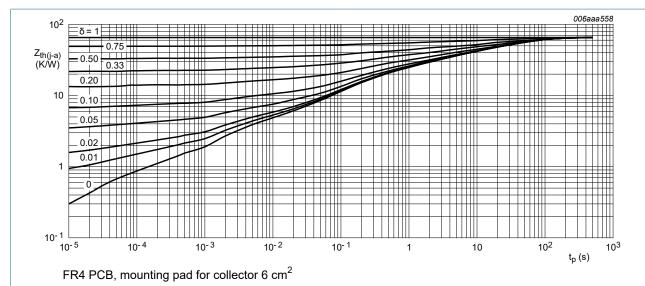


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

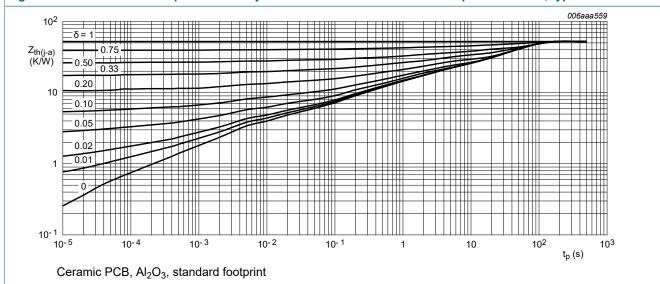


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

### 10. Characteristics

**Table 7. Characteristics** 

| Symbol           | Parameter                      | Conditions  | Min | Тур | Max  | Unit |
|------------------|--------------------------------|---|-----|-----|------|------|
| I <sub>CBO</sub> | collector-base cut-off current | V <sub>CB</sub> = -60 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C | -   | -   | -100 | nA   |
|                  |                                | $V_{CB} = -60 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$       | -   | -   | -50  | μΑ   |
| I <sub>EBO</sub> | emitter-base cut-off current   | $V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$     | -   | -   | -100 | nA   |

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| Symbol             | Parameter                               | Conditions  | Min | Тур   | Max   | Unit |
|--------------------|---|---|-----|-------|-------|------|
| h <sub>FE</sub>    | DC current gain                         | $V_{CE}$ = -2 V; $I_{C}$ = -0.5 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                | 200 | 295   | -     |      |
|                    |   | $V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                  | 200 | 270   | -     |      |
|                    |   | $V_{CE}$ = -2 V; $I_{C}$ = -2 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                  | 150 | 230   | -     |      |
|                    |   | $V_{CE}$ = -2 V; $I_{C}$ = -4 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                  | 120 | 170   | -     |      |
|                    |   | $V_{CE}$ = -2 V; $I_{C}$ = -6 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                  | 60  | 100   | -     |      |
| V <sub>CEsat</sub> | collector-emitter saturation voltage    | $I_C$ = -0.5 A; $I_B$ = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                   | -   | -35   | -50   | mV   |
|                    |   | $I_C$ = -1 A; $I_B$ = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                     | -   | -65   | -90   | mV   |
|                    |   | $I_C$ = -1 A; $I_B$ = -10 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                       | -   | -130  | -190  | mV   |
|                    |   | $I_C$ = -2 A; $I_B$ = -40 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                       | -   | -155  | -220  | mV   |
|                    |   | $I_C$ = -4 A; $I_B$ = -200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                      | -   | -195  | -275  | mV   |
|                    |   | $I_C$ = -4 A; $I_B$ = -400 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                      | -   | -150  | -210  | mV   |
|                    |   | $I_C$ = -4.2 A; $I_B$ = -210 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                  | -   | -220  | -310  | mV   |
| R <sub>CEsat</sub> | collector-emitter saturation resistance | $I_C$ = -2 A; $I_B$ = -40 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                       | -   | 78    | 110   | mΩ   |
|                    |   | $I_C$ = -4 A; $I_B$ = -200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                      | -   | 48    | 69    | mΩ   |
| V <sub>BEsat</sub> | base-emitter saturation voltage         | $I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                    | -   | -0.81 | -0.9  | V    |
|                    |   | $I_C$ = -4 A; $I_B$ = -400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                    | -   | -0.93 | -1.05 | V    |
| $V_{BEon}$         | base-emitter turn-on voltage            | $V_{CE}$ = -2 V; $I_{C}$ = -2 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C                  | -   | -0.77 | -0.85 | V    |
| d                  | delay time                              | V <sub>CC</sub> = -12.5 V; I <sub>C</sub> = -3 A; I <sub>Bon</sub> = -0.15 A;                           | -   | 15    | -     | ns   |
| t <sub>r</sub>     | rise time                               | I <sub>Boff</sub> = 0.15 A; T <sub>amb</sub> = 25 °C  | -   | 65    | -     | ns   |
| on                 | turn-on time                            |   | -   | 80    | -     | ns   |
| s                  | storage time                            |   | -   | 225   | -     | ns   |
| f                  | fall time                               |   | -   | 95    | -     | ns   |
| off                | turn-off time                           |   | -   | 320   | -     | ns   |
| fτ                 | transition frequency                    | $V_{CE}$ = -10 V; $I_{C}$ = -100 mA; f = 100 MHz; $T_{amb}$ = 25 °C                                     | -   | 130   | -     | MHz  |
| C <sub>c</sub>     | collector capacitance                   | $V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$<br>f = 1 MHz; $T_{amb} = 25 \text{ °C}$ | -   | 90    | 120   | pF   |

#### 60 V, 4.2 A PNP low VCEsat transistor

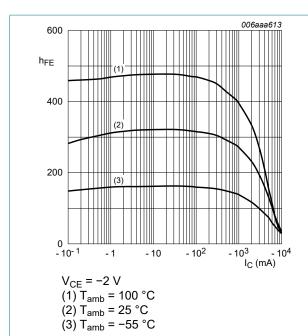


Fig. 5. DC current gain as a function of collector current; typical values

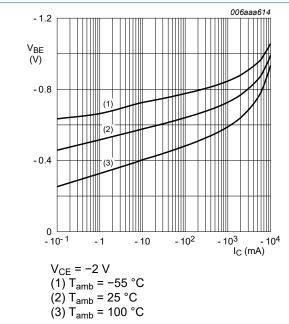


Fig. 7. Base-emitter voltage as a function of collector current; typical values

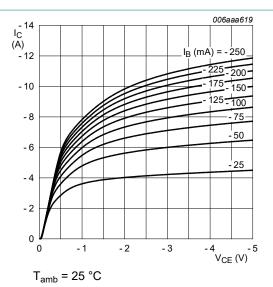
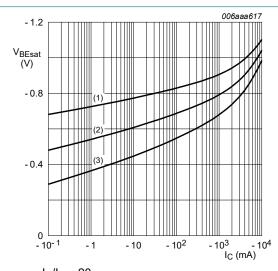


Fig. 6. Collector current as a function of collectoremitter voltage; typical values



 $I_C/I_B = 20$ (1)  $T_{amb} = -55 \,^{\circ}C$ 

(2) T<sub>amb</sub>= 25 °C (3) T<sub>amb</sub> = 100 °C

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

#### 60 V, 4.2 A PNP low VCEsat transistor

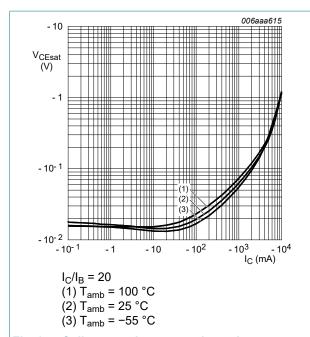


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

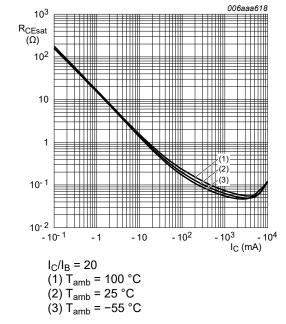


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

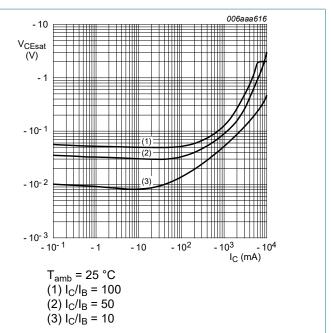


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

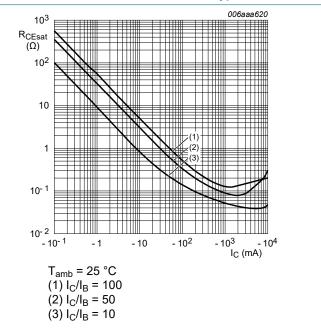
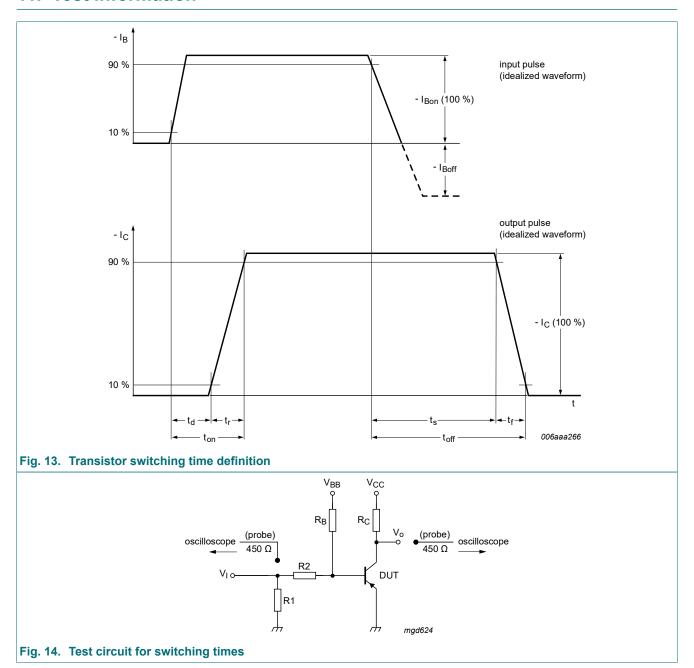


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

60 V, 4.2 A PNP low VCEsat transistor

## 11. Test information

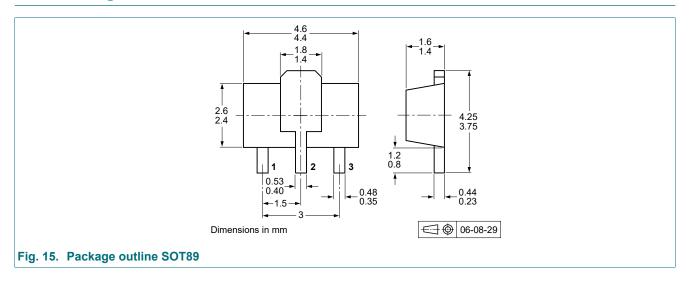


### **Quality information**

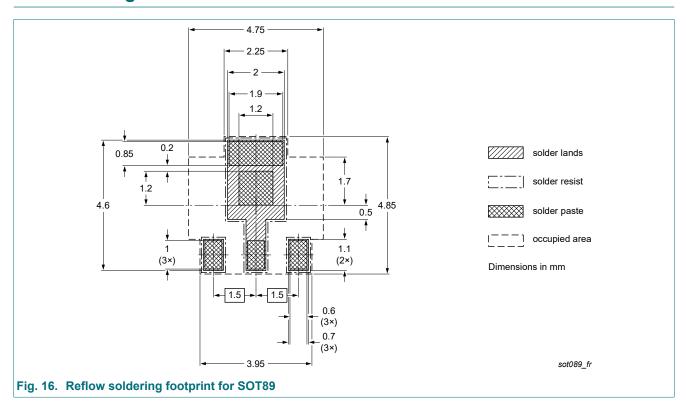
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

60 V, 4.2 A PNP low VCEsat transistor

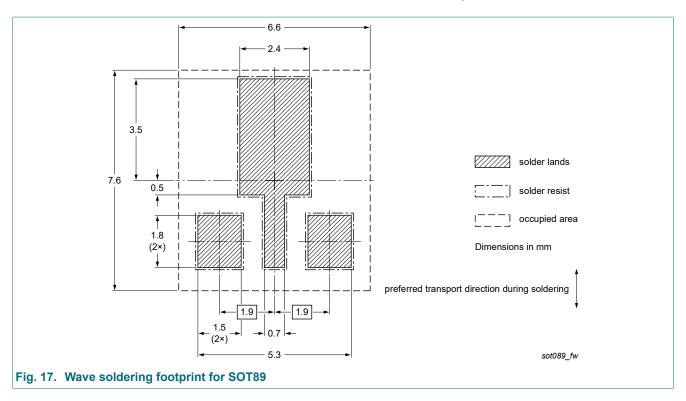
# 12. Package outline



# 13. Soldering



### 60 V, 4.2 A PNP low VCEsat transistor



60 V, 4.2 A PNP low VCEsat transistor

# 14. Revision history

### **Table 8. Revision history**

| Data sheet ID   | Release date | Data sheet status  | Change notice | Supersedes |
|-----------------|--------------|--------------------|---------------|------------|
| PBSS304PX-Q v.1 | 20231109     | Product data sheet | -             | -          |

### 60 V, 4.2 A PNP low VCEsat transistor

## 15. Legal information

#### **Data sheet status**

| Document status [1][2]         | Product<br>status [3] | Definition  |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet   | Development           | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification         | This document contains data from the preliminary specification.                       |
| Product [short]<br>data sheet  | Production            | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 9 November 2023

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